IN THE CLAIMS

Please amend the claims as follows:

Claims 1-6 (Canceled).

Claim 7 (New): A susceptor that is used in semiconductor epitaxial growth, comprising:

a barrel type susceptor having a plurality of surfaces on an outer side of each of which a plurality of substrates is freely disposed; and

a member that has the barrel type susceptor disposed inside thereof and surfaces each of which is oppositely disposed tilting in a same direction as each of the surfaces of the barrel type susceptor.

Claim 8 (New): The susceptor according to claim 7, wherein each of surfaces on a side of the barrel type susceptor of the member allows placing a plurality of substrates.

Claim 9 (New): The susceptor according to claim 7, wherein either one or both of the barrel type susceptor and the member are a heater.

Claim 10 (New): The susceptor according to claim 7, wherein the susceptor is made of a base material containing graphite.

Claim 11 (New): The susceptor according to claim 10, wherein the susceptor is covered with polycrystalline silicon carbide or polycrystalline tantalum carbide.

Claim 12 (New): A susceptor that is used in semiconductor epitaxial growth, comprising:

a barrel type susceptor having a plurality of surfaces on an inner side of each of which a plurality of substrates is freely disposed; and

a member that has the barrel type susceptor disposed at the peripheral portion thereof and surfaces each of which is oppositely disposed tilting in a same direction as each of the surfaces of the barrel type susceptor.

Claim 13 (New): The susceptor according to claim 12, wherein each of surfaces on a side of the barrel type susceptor of the member allows placing a plurality of substrates.

Claim 14 (New): The susceptor according to claim 12, wherein either one or both of the barrel type susceptor and the member are a heater.

Claim 15 (New): The susceptor according to claim 12, wherein the susceptor is made of a base material containing graphite.

Claim 16 (New): The susceptor according to claim 15, wherein the susceptor is covered with polycrystalline silicon carbide or polycrystalline tantalum carbide.